

RB521S30

200 mA low V_F MEGA Schottky barrier rectifier Rev. 01 — 6 October 2009

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

Average forward current: I_{F(AV)} ≤ 0.2 A

Reverse voltage: V_R ≤ 30 V

Low reverse current: $I_R \le 30 \mu A$

AEC-Q101 qualified

Ultra small and flat lead SMD plastic package

1.3 Applications

- Low current rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. **Quick reference data** $T_i = 25 \,^{\circ}C$ unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-------------------------|--|-------|-----|-----|------|
| I _{F(AV)} | average forward current | square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$ | | | | |
| | | T _{amb} ≤ 120 °C | [1] _ | - | 0.2 | Α |
| | | $T_{sp} \le 140 ^{\circ}C$ | - | - | 0.2 | Α |
| I _R | reverse current | $V_R = 10 V$ | - | 2.5 | 30 | μΑ |
| V_R | reverse voltage | | - | - | 30 | V |
| V_{F} | forward voltage | $I_F = 0.2 A$ | [2] | 420 | 500 | mV |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, mounting pad for cathode 1 cm².



^[2] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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2. Pinning information

Table 2. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|-------------|--------------------|----------------|
| 1 | cathode | <u>[1]</u> | |
| 2 | anode | | 1 - 2 |
| | | | sym001 |

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| RB521S30 | SC-79 | plastic surface-mounted package; 2 leads | SOD523 |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| RB521S30 | ZB |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------------------|--|--------------|-----|------|
| V_R | reverse voltage | $T_j = 25 ^{\circ}C$ | - | 30 | V |
| $I_{F(AV)}$ | average forward current | square wave; δ = 0.5; f = 20 kHz | | | |
| | | T _{amb} ≤ 120 °C | <u>[1]</u> _ | 0.2 | Α |
| | | T _{sp} ≤ 140 °C | - | 0.2 | Α |
| I _{FSM} | non-repetitive peak forward current | t _p = 8.3 ms half sine wave; JEDEC method | [2] _ | 1 | A |
| P _{tot} | total power dissipation | $T_{amb} \le 25 ^{\circ}C$ | [3][4] | 275 | mW |
| | | | [3][1] | 420 | mW |
| | | | [3][5] | 500 | mW |

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|----------------------|------------|-----|------|------|
| T_j | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -55 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [2] $T_i = 25$ °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|--|-------------|--------------|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | thermal resistance from | in free air | [1][2] | | | |
| | | [3] | - | 455 | K/W | |
| | | | <u>[4]</u> - | - | 300 | K/W |
| | | | <u>[5]</u> _ | - | 250 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | <u>[6]</u> _ | - | 90 | K/W |

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Soldering point of cathode tab.

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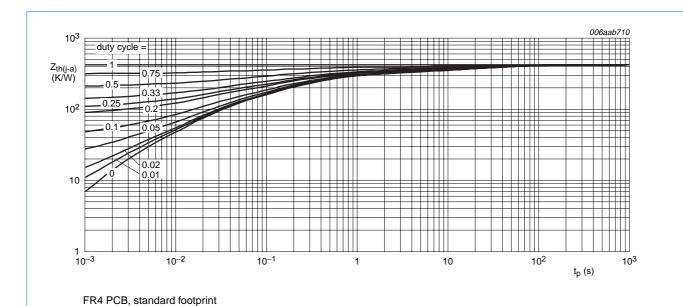
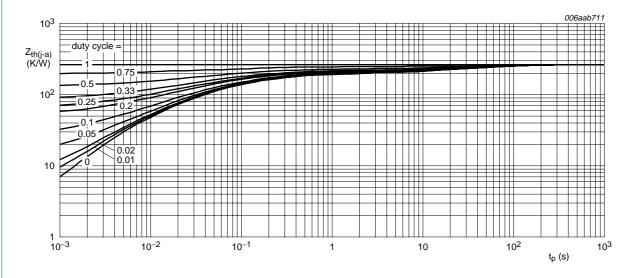


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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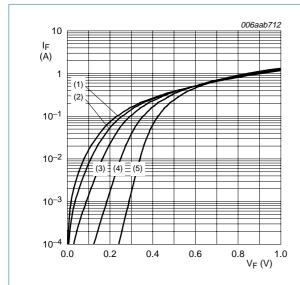
7. Characteristics

Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

| | <u> </u> | | | | | |
|--------------------------------|------------------------|-------------------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _F forward voltage | | <u>[1]</u> | | | | |
| | $I_F = 0.1 \text{ mA}$ | - | 130 | 190 | mV | |
| | | $I_F = 1 \text{ mA}$ | - | 190 | 250 | mV |
| | | $I_F = 10 \text{ mA}$ | - | 255 | 300 | mV |
| | $I_F = 100 \text{ mA}$ | - | 355 | 410 | mV | |
| | | I _F = 200 mA | - | 420 | 500 | mV |
| I _R | reverse current | V _R = 10 V | - | 2.5 | 30 | μΑ |
| C _d | diode capacitance | $f = 1 MHz; V_R = 1 V$ | - | 20 | 25 | pF |
| | | | | | | |

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$





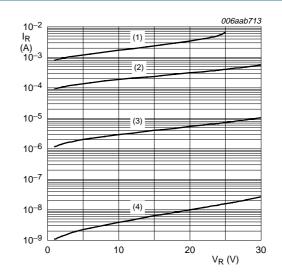
(2)
$$T_j = 125 \,^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_j = 25 \, ^{\circ}C$$

(5)
$$T_j = -40 \, ^{\circ}C$$

Fig 3. Forward current as a function of forward voltage; typical values



(1) $T_j = 125 \,^{\circ}C$

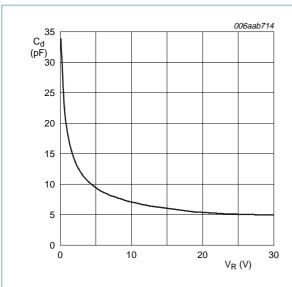
(2)
$$T_i = 85 \,^{\circ}\text{C}$$

(3)
$$T_i = 25 \,^{\circ}C$$

(4)
$$T_j = -40 \, ^{\circ}C$$

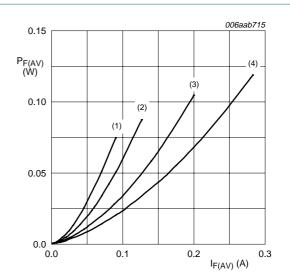
Fig 4. Reverse current as a function of reverse voltage; typical values

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 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

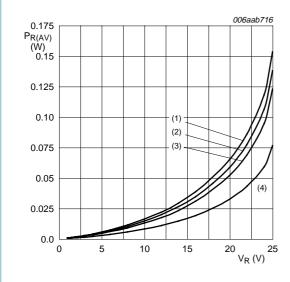
Fig 5. Diode capacitance as a function of reverse voltage; typical values



T_j = 150 °C

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

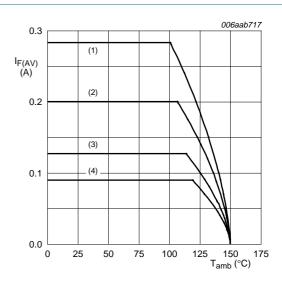
Fig 6. Average forward power dissipation as a function of average forward current; typical values



T_j = 125 °C

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

Fig 7. Average reverse power dissipation as a function of reverse voltage; typical values



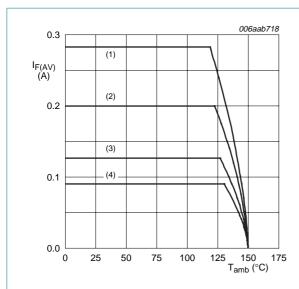
FR4 PCB, standard footprint

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 8. Average forward current as a function of ambient temperature; typical values

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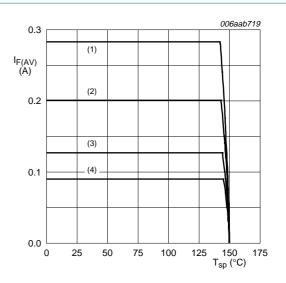
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FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

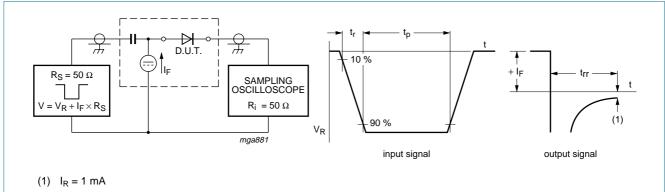
Fig 9. Average forward current as a function of ambient temperature; typical values



- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 10. Average forward current as a function of solder point temperature; typical values

8. Test information

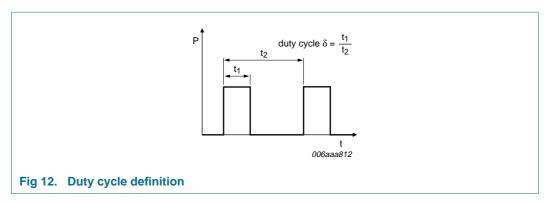


Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty cycle δ = 0.05 Oscilloscope: rise time t_r = 0.35 ns

Fig 11. Reverse recovery time test circuit and waveforms

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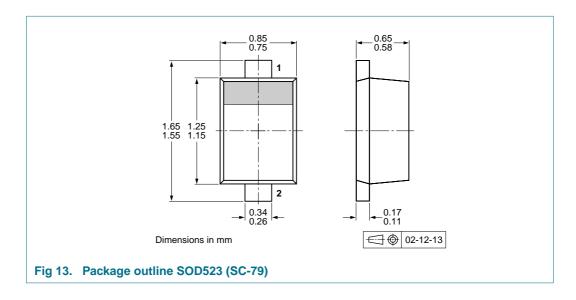


The current ratings for the typical waveforms as shown in Figure 8, 9 and 10 are calculated according to the equations: $I_{F(AV)}=I_M\times\delta$ with I_M defined as peak current, $I_{RMS}=I_{F(AV)}$ at DC, and $I_{RMS}=I_M\times\sqrt\delta$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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10. Packing information

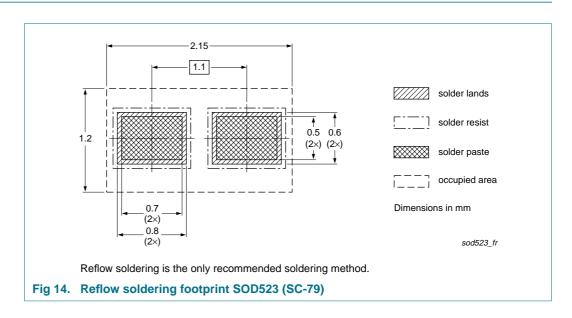
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packin | g quanti | ty |
|-------------|---------|--------------------------------|--------|----------|-------|
| | | | 3000 | 8000 | 10000 |
| RB521S30 | SOD523 | 2 mm pitch, 8 mm tape and reel | - | -315 | - |
| | | 4 mm pitch, 8 mm tape and reel | -115 | - | -135 |

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 9. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------|--------------|--------------------|---------------|------------|
| RB521S30_1 | 20091006 | Product data sheet | - | - |

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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- [2] The term 'short data sheet' is explained in section "Definitions"
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